



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23 Plastic-Encapsulate Transistors

FMMT4124 TRANSISTOR (NPN)**FEATURES**

Power dissipation

 P_{CM} : 0.33W (Tamb=25)

Collector current

 I_{CM} : 0.2A

Collector-base voltage

 $V_{(BR)CBO}$: 30V

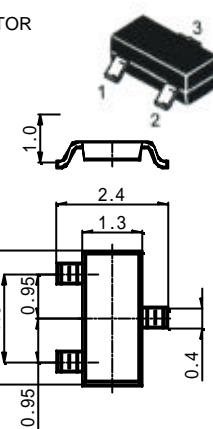
Operating and storage junction temperature range

 T_J , T_{stg} : -55 to +150**SOT-23**

1. BASE

2. Emitter

3. Collector



Unit:mm

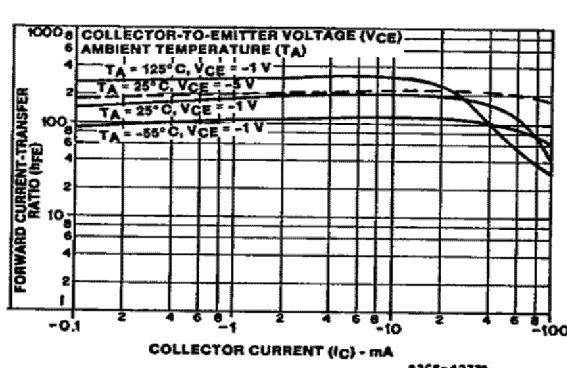
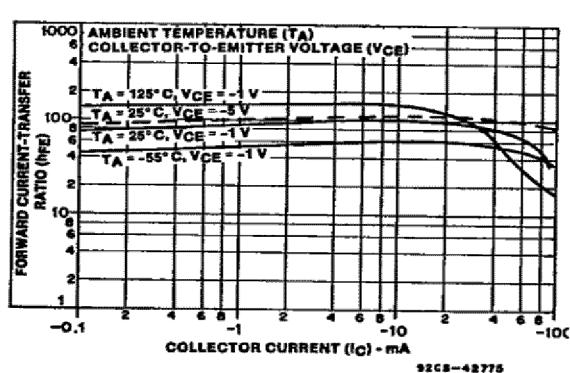
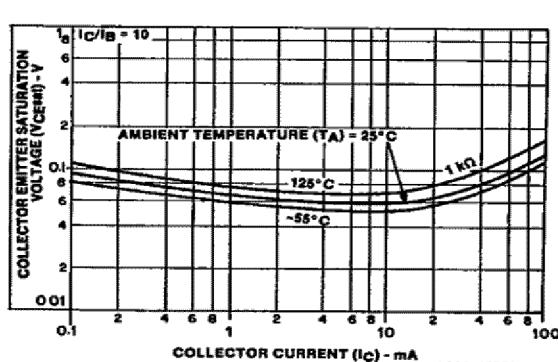
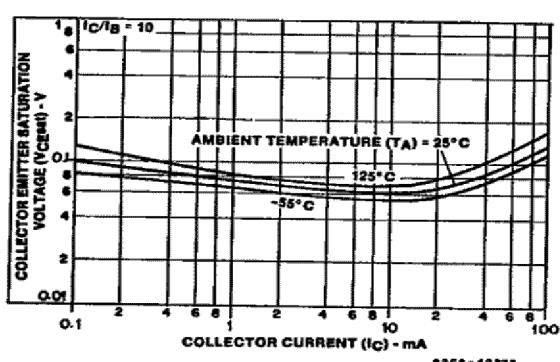
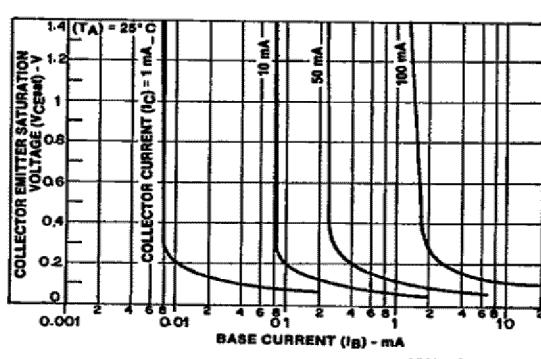
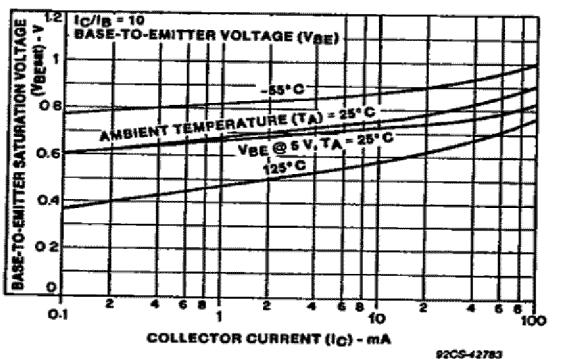
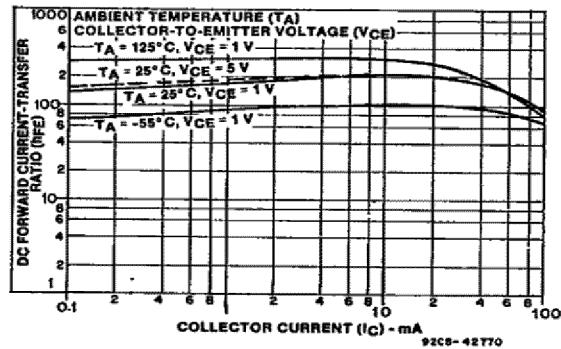
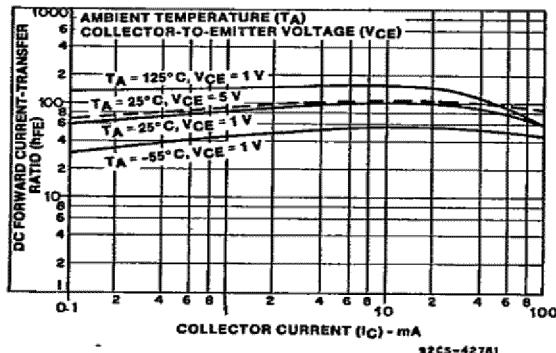
ELECTRICAL CHARACTERISTICS (Tamb=25 unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10 \mu A$, $I_E=0$	30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C= 1mA$, $I_B=0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E= 10 \mu A$, $I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}= 20 V$, $I_E=0$			0.05	μA
Emitter cut-off current	I_{EBO}	$V_{EB}= 3V$, $I_C=0$			0.05	μA
DC current gain	H_{FE}	$V_{CE}= 1V$, $I_C= 2mA$	120		360	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50 mA$, $I_B= 5mA$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=50 mA$, $I_B= 5mA$			0.95	V
Transition frequency	f_T	$V_{CE}=20V$, $I_C= 10mA$ $f = 100MHz$	300			MHz

Marking	FMMT4124 : 2C
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Typical Characteristics

FMMT4124



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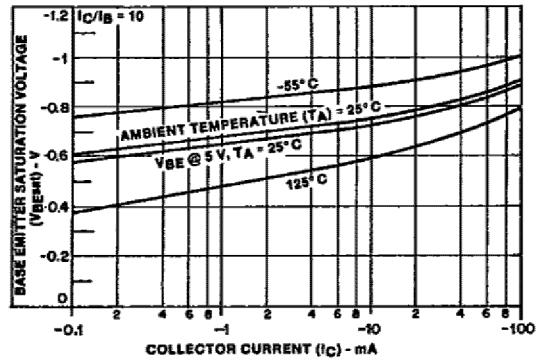


Fig. 9—Typical base-to-emitter saturation voltage characteristics for 2N4125 and 2N4126.

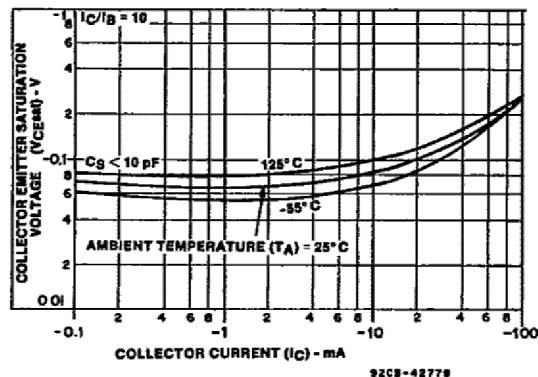


Fig. 11—Typical collector-to-emitter saturation voltage characteristics for 2N4125.

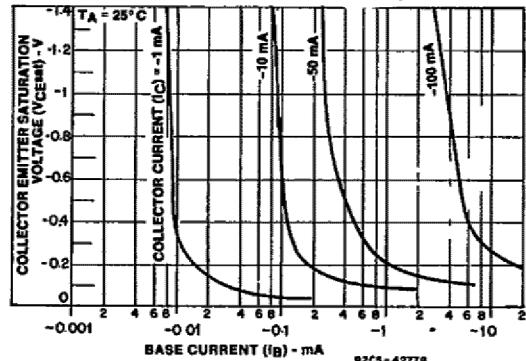


Fig. 10—Typical collector-to-emitter saturation voltage characteristics for 2N4125 and 2N4126.

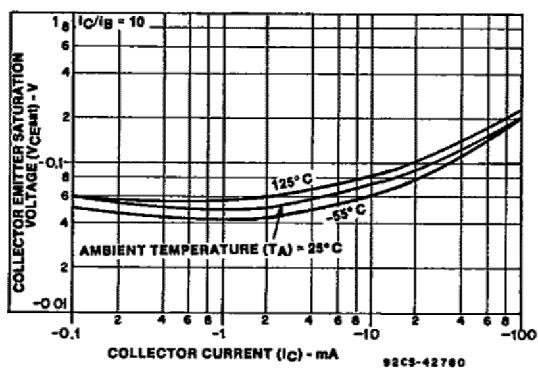


Fig. 12—Typical collector-to-emitter saturation voltage characteristics for 2N4126.